



# FAST CMOS OCTAL BIDIRECTIONAL TRANSCEIVER

**IDT54/74FCT245T/AT/CT**

## FEATURES:

- Std., A, and C grades
- Low input and output leakage  $\leq 1\mu\text{A}$  (max.)
- CMOS power levels
- True TTL input and output compatibility:
  - $V_{OH} = 3.3V$  (typ.)
  - $V_{OL} = 0.3V$  (typ.)
- High Drive outputs (-15mA  $I_{OH}$ , 64mA  $I_{OL}$ )
- Meets or exceeds JEDEC standard 18 specifications
- Military product compliant to MIL-STD-883, Class B and DESC listed (dual marked)
- Power off disable outputs permit "live insertion"
- Available in the following packages:
  - Industrial: SOIC, SSOP, QSOP, TSSOP
  - Military: CERDIP, LCC

## DESCRIPTION:

The IDT octal bidirectional transceivers are built using an advanced dual metal CMOS technology. The FCT245T is designed for asynchronous two-way communication between data buses. The transmit/receive ( $T/\bar{R}$ ) input determines the direction of data flow through the bidirectional transceiver. Transmit (active high) enables data from A ports to B ports, and receive (active low) from B ports to A ports. The output enable ( $\overline{OE}$ ) input, when high, disables both A and B ports by placing them in high Z condition.

## FUNCTIONAL BLOCK DIAGRAM



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MILITARY AND INDUSTRIAL TEMPERATURE RANGES

DECEMBER 2016

## PIN CONFIGURATION



CERDIP/ SOIC/ SSOP/ QSOP/ TSSOP  
TOP VIEW



LCC  
TOP VIEW

## ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>

Symbol	Description	Max	Unit
V <sub>TERM</sub> <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7	V
V <sub>TERM</sub> <sup>(3)</sup>	Terminal Voltage with Respect to GND	-0.5 to V <sub>CC</sub> +0.5	V
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
I <sub>OUT</sub>	DC Output Current	-60 to +120	mA

### NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed V<sub>CC</sub> by +0.5V unless otherwise noted.
- Inputs and V<sub>CC</sub> terminals only.
- Output and I/O terminals only.

## CAPACITANCE (T<sub>A</sub> = +25°C, F = 1.0MHz)

Symbol	Parameter <sup>(1)</sup>	Conditions	Typ.	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	6	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = 0V	8	12	pF

### NOTE:

- This parameter is measured at characterization but not tested.

## PIN DESCRIPTION

Pin Names	Description
$\overline{OE}$	Output Enable Inputs (Active LOW)
$\overline{T/R}$	Transmit/Receive Input
A <sub>0</sub> - A <sub>7</sub>	Side A Inputs or 3-State Outputs
B <sub>0</sub> - B <sub>7</sub>	Side B Inputs or 3-State Outputs

## FUNCTION TABLE<sup>(1)</sup>

Inputs		Outputs
$\overline{OE}$	$\overline{T/R}$	
L	L	Bus B Data to Bus A
L	H	Bus A Data to Bus B
H	X	High Z State

### NOTE:

- H = HIGH Voltage Level  
X = Don't Care  
L = LOW Voltage Level  
Z = High Impedance

## DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial:  $T_A = -40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ,  $V_{CC} = 5.0\text{V} \pm 5\%$ ; Military:  $T_A = -55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ,  $V_{CC} = 5.0\text{V} \pm 10\%$

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$V_{IH}$	Input HIGH Level	Guaranteed Logic HIGH Level		2	—	—	V
$V_{IL}$	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
$I_{IH}$	Input HIGH Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_I = 2.7\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{IL}$	Input LOW Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_I = 0.5\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{OZH}$	High Impedance Output Current (3-State output pins) <sup>(4)</sup>	$V_{CC} = \text{Max.}$	$V_O = 2.7\text{V}$	—	—	$\pm 1$	$\mu\text{A}$
$I_{OZL}$			$V_O = 0.5\text{V}$	—	—	$\pm 1$	
$I_I$	Input HIGH Current <sup>(4)</sup>	$V_{CC} = \text{Max.}, V_I = V_{CC} (\text{Max.})$		—	—	$\pm 1$	$\mu\text{A}$
$V_{IK}$	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		—	-0.7	-1.2	V
$V_H$	Input Hysteresis	—		—	200	—	mV
$I_{CC}$	Quiescent Power Supply Current	$V_{CC} = \text{Max.}, V_{IN} = \text{GND or } V_{CC}$		—	0.01	1	mA

## OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$V_{OH}$	Output HIGH Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -6\text{mA MIL}$ $I_{OH} = -8\text{mA IND}$	2.4	3.3	—	V
			$I_{OH} = -12\text{mA MIL}$ $I_{OH} = -15\text{mA IND}$	2	3	—	
$V_{OL}$	Output LOW Voltage	$V_{CC} = \text{Min.}$ $V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 48\text{mA MIL}$ $I_{OL} = 64\text{mA IND}$	—	0.3	0.55	V
$I_{OS}$	Short Circuit Current	$V_{CC} = \text{Max.}, V_O = \text{GND}^{(3)}$		-60	-120	-225	mA

### NOTES:

- For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at  $V_{CC} = 5.0\text{V}$ ,  $+25^{\circ}\text{C}$  ambient.
- Not more than one output should be tested at one time. Duration of the test should not exceed one second.
- The test limit for this parameter is  $\pm 5\mu\text{A}$  at  $T_A = -55^{\circ}\text{C}$ .

## POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions <sup>(1)</sup>		Min.	Typ. <sup>(2)</sup>	Max.	Unit
$\Delta I_{CC}$	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	0.5	2	mA
$I_{CCD}$	Dynamic Power Supply Current <sup>(4)</sup>	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE} = T/\overline{R} = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	0.15	0.25	mA/ MHz
$I_C$	Total Power Supply Current <sup>(6)</sup>	$V_{CC} = \text{Max.}$ Outputs Open $f_i = 10\text{MHz}$ 50% Duty Cycle $\overline{OE} = T/\overline{R} = \text{GND}$ One Bit Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	1.5	3.5	mA
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	1.8	4.5	
		$V_{CC} = \text{Max.}$ Outputs Open $f_i = 2.5\text{MHz}$ 50% Duty Cycle $\overline{OE} = T/\overline{R} = \text{GND}$ Eight Bits Toggling	$V_{IN} = V_{CC}$ $V_{IN} = \text{GND}$	—	3	6 <sup>(5)</sup>	
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	5	14 <sup>(5)</sup>	

### NOTES:

- For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
  - Typical values are at  $V_{CC} = 5.0V$ ,  $+25^\circ\text{C}$  ambient.
  - Per TTL driven input; ( $V_{IN} = 3.4V$ ). All other inputs at  $V_{CC}$  or  $\text{GND}$ .
  - This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
  - Values for these conditions are examples of  $\Delta I_{CC}$  formula. These limits are guaranteed but not tested.
  - $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$   
 $I_C = I_{CC} + \Delta I_{CC} D_{HNT} + I_{CCD} (f_{CP}/2 + f_i N_i)$   
 $I_{CC}$  = Quiescent Current  
 $\Delta I_{CC}$  = Power Supply Current for a TTL High Input ( $V_{IN} = 3.4V$ )  
 $D_H$  = Duty Cycle for TTL Inputs High  
 $N_T$  = Number of TTL Inputs at  $D_H$   
 $I_{CCD}$  = Dynamic Current caused by an Input Transition Pair (HLH or LHL)  
 $f_{CP}$  = Clock Frequency for Register Devices (Zero for Non-Register Devices)  
 $f_i$  = Output Frequency  
 $N_i$  = Number of Outputs at  $f_i$
- All currents are in milliamps and all frequencies are in megahertz.

### SWITCHING CHARACTERISTICS OVER OPERATING RANGE - INDUSTRIAL

Symbol	Parameter	Condition <sup>(1)</sup>	74FCT245AT		74FCT245CT		Unit
			Min. <sup>(2)</sup>	Max.	Min. <sup>(2)</sup>	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A to B, B to A	CL = 50pF RL = 500Ω	1.5	4.6	1.5	4.1	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time $\overline{OE}$ to A or B		1.5	6.2	1.5	5.8	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time $\overline{OE}$ to A or B		1.5	5	1.5	4.8	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time T/ $\overline{R}$ to A or B <sup>(3)</sup>		1.5	6.2	1.5	5.8	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time T/ $\overline{R}$ to A or B <sup>(3)</sup>		1.5	5	1.5	4.8	ns

### SWITCHING CHARACTERISTICS OVER OPERATING RANGE - MILITARY

Symbol	Parameter	Condition <sup>(1)</sup>	54FCT245T		54FCT245AT		54FCT245CT		Unit
			Min. <sup>(2)</sup>	Max.	Min. <sup>(2)</sup>	Max.	Min. <sup>(2)</sup>	Max.	
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A to B, B to A	CL = 50pF RL = 500Ω	1.5	7.5	1.5	4.9	1.5	4.5	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time $\overline{OE}$ to A or B		1.5	10	1.5	6.5	1.5	6.2	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time $\overline{OE}$ to A or B		1.5	10	1.5	6	1.5	5.2	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time T/ $\overline{R}$ to A or B <sup>(3)</sup>		1.5	10	1.5	6.5	1.5	6.2	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time T/ $\overline{R}$ to A or B <sup>(3)</sup>		1.5	10	1.5	6	1.5	5.2	ns

**NOTES:**

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not tested.

## TEST CIRCUITS AND WAVEFORMS



Octal Link

*Test Circuits for All Outputs*



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*Set-Up, Hold, and Release Times*



Octal Link

*Propagation Delay*

## SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

### DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.  
RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



*Pulse Width*

Octal Link



Octal Link

*Enable and Disable Times*

### NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- Pulse Generator for All Pulses: Rate  $\leq 1.0\text{MHz}$ ;  $t_r \leq 2.5\text{ns}$ ;  $t_f \leq 2.5\text{ns}$ .

## ORDERING INFORMATION



## Datasheet Document History

09/29/2009	Pg. 7	Updated the ordering information by removing the "IDT" notation and non RoHS part.
12/12/2016	Pg. 7	Updated the ordering information by adding detailed package information and Tape & Reel.



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- Техническая поддержка проекта;
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